







Part 4

Design Methodology-Application to Low Noise Amplifier 具線具



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https://github.com/ACMmodel/MOSFET_model https://colab.research.google.com/drive/1s3PKF6pf3zIhlTj6jcqhCLlcGfJ_UEE?usp=sharing#scrollTo=EMGo7aUzyukW



TiM Agenda

- Overview of Design Methods for RFIC
- LNA Design Considerations
- Resistive Feedback LNA
- What we need in ACM-2
- Inversion Level Based Method for R-Feedback LNA with ACM-2

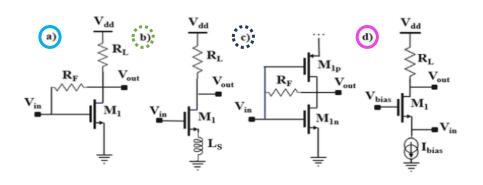


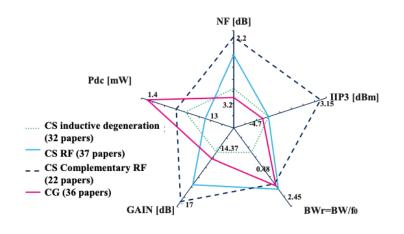
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• 1st Step: Architecture Choice





• 2nd Step: Circuit Analysis





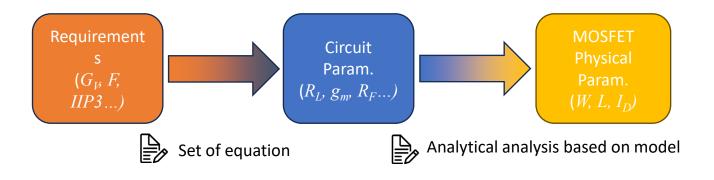




$$|G_T| = |G_v|Q_{IN} = \frac{(G_m R_F - 1)R_O}{(R_O + R_F)} \sqrt{1 + Q_P^2}$$

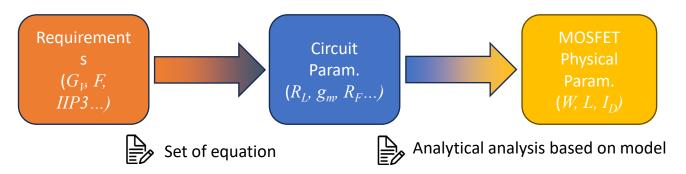


• 3rd Step: Circuit Sizing





• 3rd Step: Circuit Sizing



Region based model

sat.
$$I_d = 2.K_n \frac{W}{L} \left[(V_{gs} - V_t) V_{ds} - \frac{V_{ds}^2}{2} \right]$$

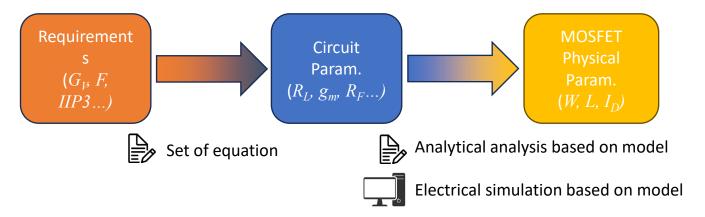
$$I_d = K_n \frac{W}{L} (V_{gs} - V_t)^2 \left(1 + \frac{k_{en}}{L} V_{ds} \right)$$

PROS: simple

CONS: Inaccurate with short channel MOS



• 3rd Step: Circuit Sizing



BSIM3 / UTSOI compact model

PROS:

- Accurate
- Direct relationship between requirements and physical parameters

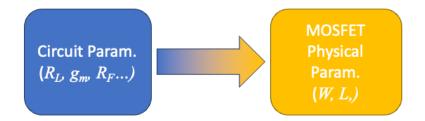
CONS:

- Increases the gap between Physic and design
- Long optimization



Overview of Design Methods for RFIC New Trends

Issue in the sizing step



 How to maintain simplicity and accuracy with the scaling and especially Short Channel Effects (SCE) at the sizing step.

?

- A possible solution
 - g_m/Id design approaches
 - LUT based
 - ACM or EKV based

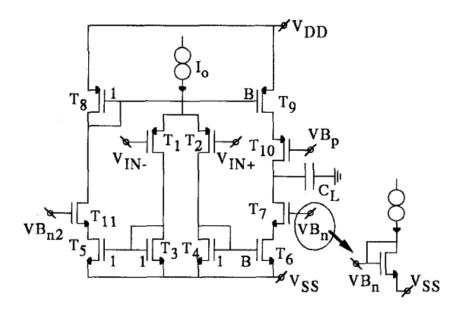


Overview of Design Methods for RFIC g_m/Id approach based on LUT

General Principle

[Silveira, Flandre, Jespers – JSSC 1996]

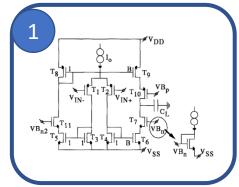
For a given structure



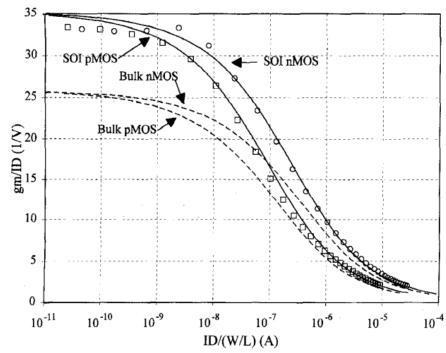


Overview of Design Methods for RFIC g_m/Id approach based on LUT

General Principle



- For a given structure
- Methods are based on
 - ⇒ Extraction of MOS parameters (LUT)
 - $I_D/(W/L)$ vs g_m/I_D
 - $g_m/I_D vs V_{gs0}$

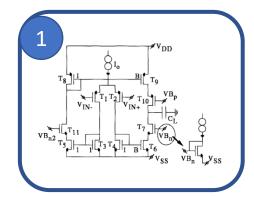


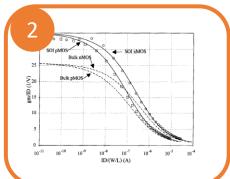


TIMA Overview of Design Methods for RFIC

g_m/Id approach based on LUT

General Principle





- For a given structure
- Methods are based on
 - ⇒ Extraction of MOS parameters (LUT)
 - $I_D/(W/L)$ vs g_m/I_D
 - $g_m/I_D vs V_{gs0}$
 - \Rightarrow Set of equations

$$SR = \frac{B \cdot I_{D1}}{C_L}$$

$$f_T = \frac{B \cdot g_{m1}}{2\Pi \cdot C_L}$$
(5)

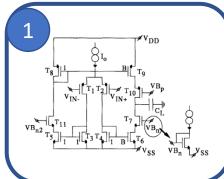
$$A_0 = \left(\frac{g_m}{I_D}\right)_1 \cdot \left(\frac{g_m}{I_D}\right)_2 \cdot \frac{1}{\frac{1}{V_{A6} \cdot V_{A7}} + \frac{1}{V_{A9} \cdot V_{A10}}}$$
(4)

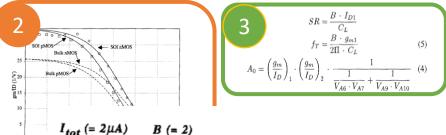


Overview of Design Methods for RFIC

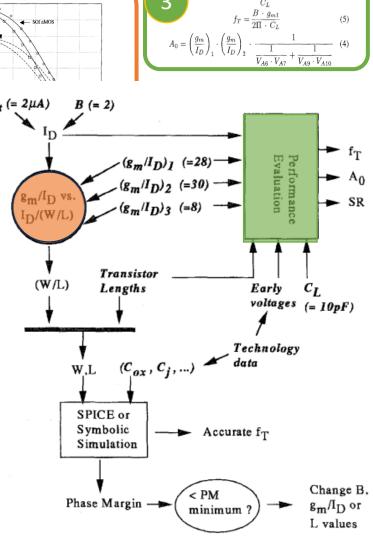
g_m/Id approach based on LUT

General Principle





- For a given structure
- Methods are based on
 - ⇒ Extraction of MOS parameters (LUT)
 - $I_D/(W/L)$ vs g_m/I_D
 - $g_m/I_D vs V_{gs0}$
 - \Rightarrow Set of equations
- Methods helps the designers in sizing the structure
- Quite used in low frequency domain





Tima Overview of Design Methods for RFIC

g_m/Id approach based on LUT

LIMITATIONS?

Time Consuming

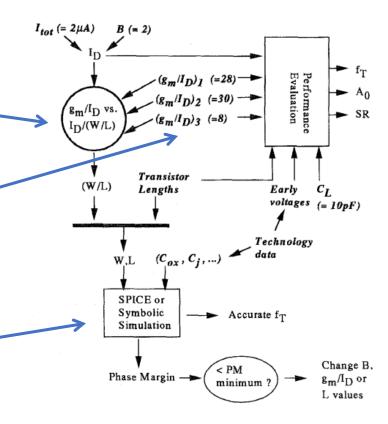


Lakes of precision (parametric set of characteristics)



Long optimization sequence

Need for a model based approach





Overview of Design Methods for RFIC g_m/Id approach based All Region Models (ACM/EKV)

All Region 3PM model

- EKV [Enz, Krummenacher, Vittoz]
- ACM [Schneider, Galup]



With a 3PM model we have:

$$\frac{g_{m}}{I_{D}} = \frac{2}{n\phi_{t}\left(1 + \sqrt{1 + i_{f}}\right)} \qquad g_{m} = \frac{2I_{S}}{\phi_{t}}\left(\sqrt{1 + i_{f}} - 1\right) \qquad V_{P} - V_{S(D)} = \phi_{t}\left[\sqrt{1 + i_{f(r)}} - 2 + \ln\left(\sqrt{1 + i_{f(r)}} - 1\right)\right] \qquad V_{P} \approx \frac{V_{G} - V_{T0}}{n}$$

- PROS: The sizing is straightforward
- CONS: Inaccurate with SCE

Non-linearities can't be captured gds effect can't be captured



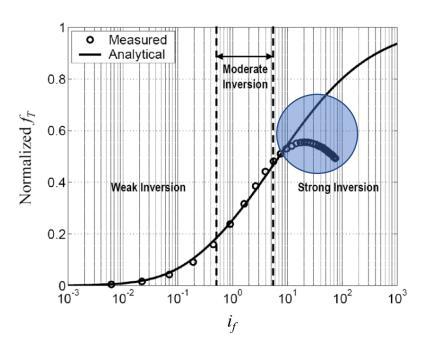
Can we design RFICs?

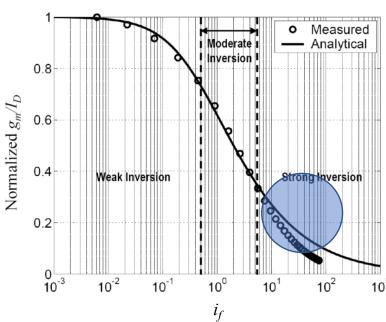


Design Regions



• f_t grows with i_f

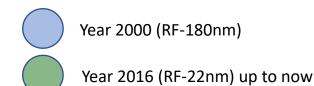


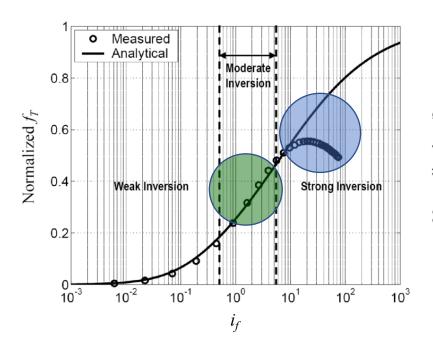


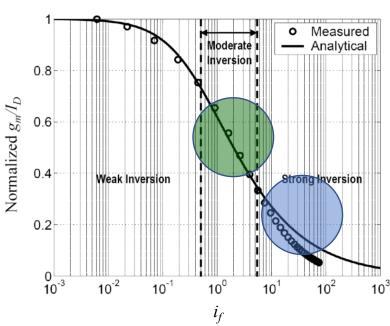


Design Regions

• f_t grows with i_f but g_m/I_D reduces with i_f









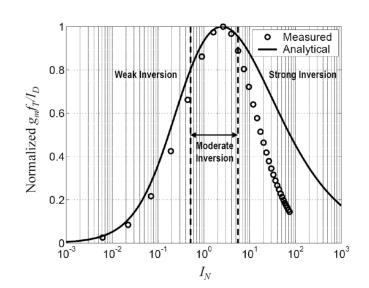
$g_m f/I_D$: A First Approach

For RF design

- A. Shameli et P. Heydari, « Ultra-Low Power RFIC Design Using Moderately Inverted MOSFETs: An Analytical/Experimental Study », RFCI, 2004.
- A FOM that maximize the gain bandwidth product

$$\frac{g_m f_T}{I_D}$$

Gives the i_f that produces the best GBW product



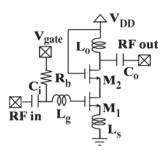
- Not optimal:
 - o the gain or the bandwidth might be oversized.
 - Do not depends on the topology

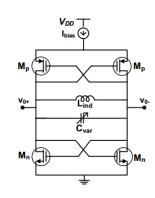


LNA

Function Based FoM

- For a given Function
- Define a FoM for the function

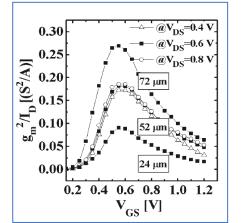




$$\text{FoM}_{\text{LNA}} = \frac{G}{(F-1) \cdot P} \propto \frac{g_m^2}{\left(\frac{I_D}{g_m^2}\right) \cdot I_D} \propto \left(\frac{g_m^2}{I_D}\right)^2$$

• Find the i_f that maximizes the FoM

I. Song et B.-G. Park, « A Simple Figure of Merit of RF MOSFET for Low-Noise Amplifier Design », Electron Device Lett. IEEE, vol. 29(12), 2008.



$$PN(\Delta f) = 10log\left(\frac{k_B T \pi^2}{64Q^2} \left(\frac{g_m}{I_D} \frac{1}{I_D} \frac{f_0}{(\Delta f)^2} \lambda\right)\right)$$

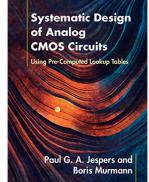
R. Fioreli; J. Núñez; F. Silveira; "All-Rnversion region gm/ID methodology for RF circuits in FinFET technologies" 2018 NEWCAS



Circuit Based Method

Circuit Sizing Based on LUT

- For a given Circuit
- Similar to the one introduced by Silveira, Flandre, Jespers in 1996
- Capacitance and noise effects can be captured in LUT for bandwidth and noise analysis
- Well known and well referenced
- But ...
- Still complicated
- The gap between physics and design remains
- No analytical relationships to size « by hand »





Circuit Sizing Based on ACM

- Equations can be derived for a given circuit
- Quasi analytical approach
 - R-F LNA designed with 3PM-ACM [Bourdel ICECS 2019]
- Gds and gm3 (NL) are taken into account
 - R-F LNA designed with 7PM-ACM [Bouchoucha ISCAS 2023]
 - CG LNA designed with 5PM-ACM2[Alves Neto ACCESS 2024]

design-oriented mode d technologies

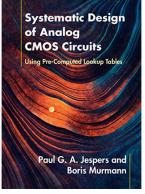
Mohamed Khalil Bouchoucha^{1,2}, Dayana A. Pinc Manuel J. Barragan ¹STMicroelectronics, 38920 Crolles, France, ²TIMA I

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is work was supported in part b

lippe Cathelin¹, Jean-Michel Fournier²,

https://github.com/ACMmodel/MOSFET model

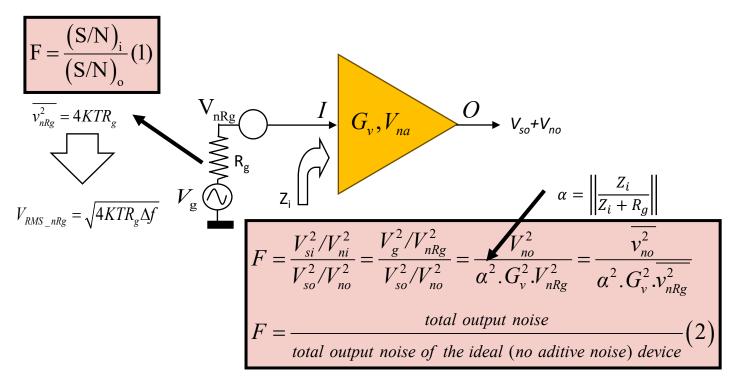




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NF is the signal to noise ratio (SNR) degradation (Eq. 1)

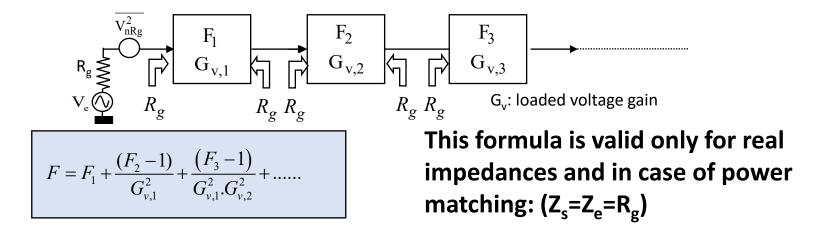


• NF also express the quantity of noise added by the stage regarding the noise delivered by the source (R_q) on Δf . (Eq. 2)



LNA Design considerations Friss Formula

>RF Basis



In RFIC, impedances are complex and never equal. This formula cannot be used as is. However, the following statements remain valid in RFIC.

The gain of the first stages reduces the NF of the following ones.



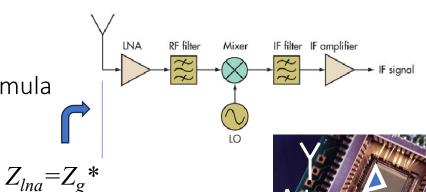
- => The receiver chain must start by amplifiers
- => The NF of the first stage must be as low as possible Note that lossy stages (G_v <1) increase the NF, especially when they are in front of the receiver chain (antenna filter, image rejection filter, antenna switch).



LNA Design considerations Input patching

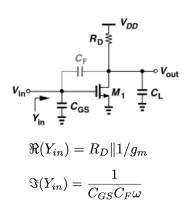
System point of vue

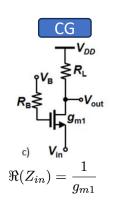
- LNA is the first device due to Friss formula
- Antenna is mainly 50 Ω .

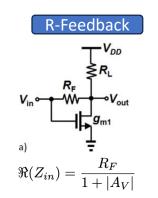


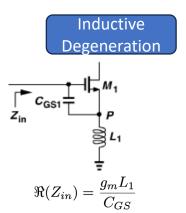
In CMOS

- Generally, the input impedance is capacitive Re (Y11) is very low
- For exemple : CS amplifier





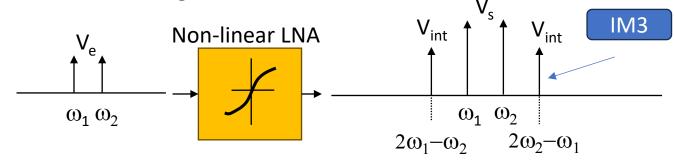


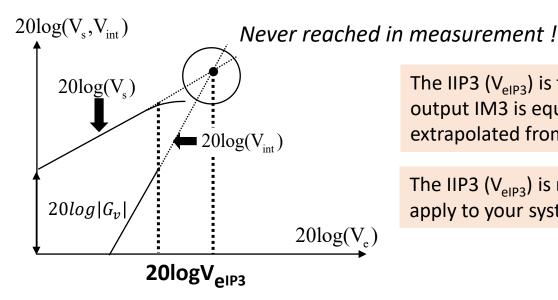




LNA Design considerations Non-Linearities

 ω_1 and ω_2 are 2 harmonics of the wanted signal





The IIP3 (V_{elP3}) is the input signal level for which the output IM3 is equaling the fundamental harmonic (Vs) extrapolated from small signal (AC).

The IIP3 (V_{eIP3}) is related to the maximum power you can apply to your system



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Resistive Feedback LNA Topology

R-Feedback general considerations

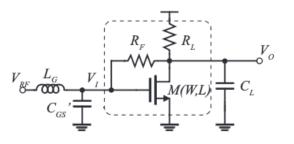
- Simple
- Compact (No-inductors)
- Wideband
- RF allows to synthesize a real part in Zin
- LG and CGS' will help in cancelling the imaginary part
- while controlling Qin

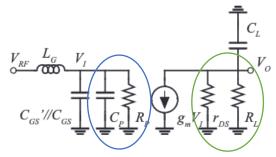
Input impedance

$$Z_{IN} = L_G s + \left(\frac{1}{(C_{GS} + C'_{GS})s} / Z_P\right)$$

$$\Re(Zp) = R_P = \frac{R_O + R_F}{1 + G_m R_O},$$

$$C_P = \frac{R_O^2 C_L (G_m R_F - 1)}{(R_O + R_F)^2}$$





$$R_O = \frac{R_L r_{DS}}{R_L + r_{DS}}$$

$$\Re(Z_{IN}) = R_S = \frac{R_P}{(1 + Q_D^2)} = 50 \ \Omega$$

$$Q_P = R_P C_T \omega_0$$

$$Q_P = R_P C_T \omega_0 \qquad C_T = C_{GS} + C'_{GS} + C_P$$

$$\Im(Z_{IN}) = 0 = L_G s + \frac{Q_P^2}{C_T s (1 + Q_P)^2}$$

Note:
$$\begin{cases} \Re(Zp) = \frac{1 + \left(\frac{f}{f_c}\right)^2}{\frac{1 + G_m R_O}{R_O + R_F} + \frac{1}{R_F} \left(\frac{f}{f_c}\right)^2}, & \text{Reduces For} \\ \Im(Zp) = -\left(1 + \frac{R_F}{R_O}\right)^2 \frac{1 + \left(\frac{f}{f_c}\right)^2}{2\pi f C_F(G_m R_F - 1)} & \frac{f_C}{f_c} = N > 3 \end{cases}$$

Reduces FO
$$\frac{f_c}{r} - N > 3$$

$$\frac{f_c}{f} = N > 3$$



Resistive Feedback LNA

Topology

Voltage Gain

$$|G_o| = \left| \frac{V_O}{V_{RF}} \right| = \frac{|G_T|}{\sqrt{\left(1 + \left(\frac{f_0}{f_c}\right)^2\right)}}$$

$$|G_T| = |G_v|Q_{IN} = \frac{(G_m R_F - 1)R_O}{(R_O + R_F)} \sqrt{1 + Q_P^2}$$

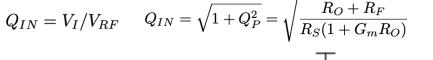


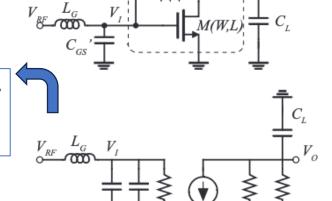
$\frac{f_c}{f_0} = N > 3$

BW

$$f_c = \frac{R_O + R_F}{2\pi R_O R_F C_L} = N f_0$$

(the source resistance seen at the $50~\Omega$ input)





Noise Figure

$$F = 1 + \frac{4\left(\frac{R_F}{Q_{IN}^2} + R_S\right)^2}{Q_{IN}^2 G_m R_S \left[\frac{R_F}{Q_{IN}^2} + R_S + \frac{G_m R_S R_F R_L}{R_F + R_L}\right]^2} \left[\gamma + \frac{1}{G_m R_L} + \frac{\left(1 + \frac{Q_{IN}^2 G_m R_S R_F}{R_F + Q_{IN}^2 R_S}\right)^2}{G_m R_F}\right]$$

$$\left(F_{min} = 1 + \frac{(1 + G_m)R_S^2 R_F}{R_S (1 - G_m R_F)^2} + \frac{\gamma g_m (R_S + R_F)^2}{R_S (1 - G_m R_F)^2} + \frac{(R_S + R_F)^2}{R_S R_L (1 - G_m R_F)^2}\right)$$

$$IIP_{\mathcal{J}}$$

$$V_{IIP3} = \frac{2}{Q_{IN}} \sqrt{\frac{2G_m}{G_{m3}}}$$



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What we need in ACM-2

Small signal parameters

Small signal (AC) parameters

 G_T , NF, IIP3 vs (G_m, G_{m3}, G_{DS})

$$g_{m} = \frac{\partial I_{D}}{\partial V_{G}} = \frac{I_{S}}{\phi_{t}} g_{G} = \frac{I_{S}}{n\phi_{t}} \frac{2(q_{s} - q_{d}) - i_{d} \zeta\left(\frac{q_{s}}{1 + q_{s}} - \frac{q_{d}}{1 + q_{d}}\right)}{1 + \zeta\left(q_{s} - q_{d}\right)}$$

$$g_{ds} = \frac{I_{S}}{\phi_{t}} g_{D} = \frac{I_{S}}{n\phi_{t}} \frac{2(q_{s}\sigma - q_{d}(\sigma - n)) - i_{d}\zeta\left(\sigma\frac{q_{s}}{1 + q_{s}} - (\sigma - n)\frac{q_{d}}{1 + q_{d}}\right)}{1 + \zeta(q_{s} - q_{d})}$$

$$g_{m3} = \frac{I_{S}}{\left(n\phi_{t}\right)^{3}} \left\{ \frac{\frac{2q_{s}}{(1+q_{s})^{3}} - \frac{2q_{d}}{(1+q_{d})^{3}} - \zeta n^{2}g_{G2}\left(\frac{q_{s}}{1+q_{s}} - \frac{q_{d}}{1+q_{d}}\right) - \zeta\left[2ng_{G}\left(\frac{q_{s}}{(1+q_{s})^{3}} - \frac{q_{d}}{(1+q_{d})^{3}}\right) + i_{d}\left(\frac{q_{d}(1-2q_{d})}{(1+q_{d})^{5}} - \frac{q_{d}(1-2q_{d})}{(1+q_{d})^{5}}\right)\right]}{1 + \zeta\left(q_{s} - q_{d}\right)} \right\}$$

- Valid in all region (qs and qd shall be explored)
- We consider only saturation

$$q_{dsat} = q_s + 1 + \frac{1}{\zeta} - \sqrt{\left(1 + \frac{1}{\zeta}\right)^2 + \frac{2q_s}{\zeta}}$$

$$g_{msat} = \frac{2I_S}{n\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)}$$

$$g_{dsat} = \frac{\sigma}{n} \frac{2I_S}{\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)}$$

$$g_{msat} = \frac{2I_S}{n\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)} \qquad g_{dsat} = \frac{\sigma}{n} \frac{2I_S}{\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)} \qquad g_{msat3} = \frac{16I_S}{(n\phi_t)^3} \frac{q_s}{(q_s + 1)^3} \frac{2 - 2\zeta q_s - 3\zeta q_s^2}{(q_s + 1)^4}$$

It reduces the exploration to only qs.



What we need in ACM-2

Small signal parameters

Large signal (DC) parameters

• To compute the final voltages

$$V_T = V_{T0} - \sigma(V_{SB} + V_{DB})$$

$$V_P = \frac{V_{GB} - V_T}{n}$$

$$\frac{V_P - V_{S(D)B}}{\phi_t} = q_{s(d)} - 1 + \ln q_{s(d)}$$

• Sometime we'll use i_f in the code

$$i_d = i_f - i_r$$
 \longleftrightarrow $q_{S(D)} = \sqrt{1 + i_{f(r)}} - 1$ \longleftrightarrow $i_d = \frac{(q_s + q_d + 2)}{1 + \zeta |q_s - q_d|} (q_s - q_d)$
 $I_D = I_S. i_d$

 $I_S = \frac{\mu C'_{ox} n(U_T)^2}{2} \frac{W}{I_S}$



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General Approach :

Requirements

- GT, NF, IIP3, IDC Possible Tradeoff
- fo, CL, BW No Tradeoff

Design parameters

- ACM parameters for a fixed L
- V_{T0} , I_S , n, σ , ζ

Design Variables (parameters)

- (W, qs) are first order design variables (qs = inversion level sets the energy efficiency and the voltages)
- RL, RF are second order design variables

Approach:

- Explore the different tradeoff (the design space) on GT, NF, IIP3 and IDC by playing with W, qs.
- In saturation region (only gs is needed)

$$g_{msat} = \frac{2I_S}{n\phi_t} \frac{q_S}{1 + \zeta(q_S + 1)} \qquad g_{msat3} = \frac{16I_S}{(n\phi_t)^3} \frac{q_S}{(q_S + 1)^3} \frac{2 - 2\zeta q_S - 3\zeta q_S^2}{(\zeta q_S + 2)^4} \qquad g_{dsat} = \sigma \frac{2I_S}{n\phi_t} \frac{q_S}{1 + \zeta(q_S + 1)}$$

Circuit equations depend on **G**m and ACM gives **g**m (normalized)...

$$|G_T| = \frac{(G_m R_F - 1)R_O}{(R_O + R_F)} \sqrt{\frac{R_O + R_F}{R_S(1 + G_m R_O)}} \quad G_{[m;DS]x} = \mu C'_{ox} \frac{(U_T)^{2-x} W}{2} I_{g[m;DS]x}$$

$$Where we introduce W in the design space
$$I_S = \mu C'_{ox} n \frac{(U_T)^2}{2} \frac{W}{L} \quad I_{SL} = I_{SL} = \mu C'_{ox} n \frac{(U_T)^2}{2} \frac{W}{L}$$$$



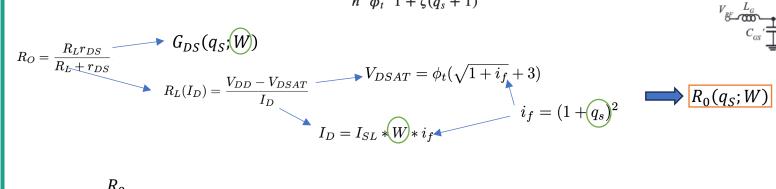
Reducing the variables:

$$|G_T| = \frac{(G_m R_F - 1)R_O}{(R_O + R_F)} \sqrt{\frac{R_O + R_F}{R_S(1 + G_m R_O)}} \quad G_T(G_m; R_0; R_F; R_S) = G_T(W; q_S; I_D; V_{DSAT}; V_{T0}; I_S; n; \sigma; \zeta; f_c; \mathcal{C}_L)$$

$$\text{variables} \quad \text{parameters}$$

$$G_{[m;DS]x} = \mu C'_{ox} \frac{(U_T)^{2-x} W}{2} G_{[m;DS]x} \longrightarrow g_{msat} = \frac{2I_S}{n\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)} \longrightarrow G_m(q_S; W)$$

$$\longrightarrow g_{dsat} = \frac{\sigma}{n} \frac{2I_S}{\phi_t} \frac{q_s}{1 + \zeta(q_s + 1)} \longrightarrow G_{DS}(q_S; W)$$



$$R_F = \frac{R_0}{2\pi R_0 C_L f_c - 1} \qquad \Longrightarrow \boxed{R_F(q_S; W) \Big|_{f_c}}$$

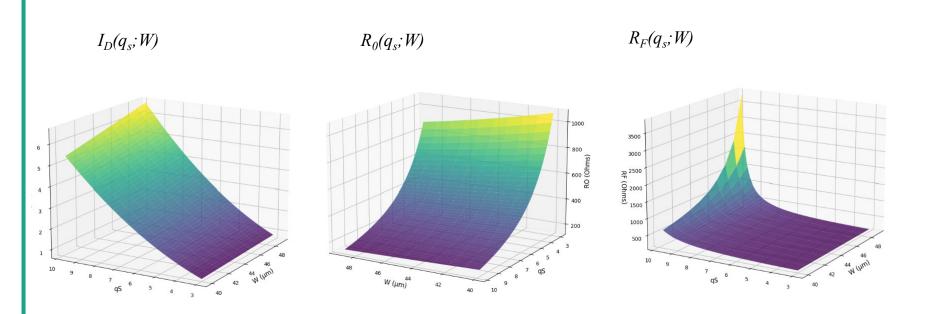
$$\left(f_c = \frac{R_O + R_F}{2\pi R_O R_F C_L}\right)$$



 $G_T(G_m; R_0; R_F; R_S) = G_T(W; q_S)$



Finally : $I_D(q_s; W)$; $R_F(q_s; W)$; $R_0(q_s; W)$; $G_T(q_s; W)$





 $\Rightarrow F(G_T; W)$

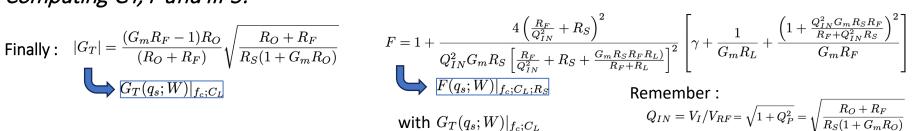
Computing GT, F and IIP3:

Finally:
$$|G_T| = \frac{(G_m R_F - 1)R_O}{(R_O + R_F)} \sqrt{\frac{R_O + R_F}{R_S(1 + G_m R_O)}}$$

$$G_T(q_s; W)|_{f_c; C_L}$$

$$V_{IIP3} = \frac{2}{Q_{IN}} \sqrt{\frac{2G_m}{G_{m3}}}$$

$$IIP_3(q_s; W)|_{f_c; C_L; R_S}$$





Exploring the design space:

Setting GT (or NF, or IIP3) helps to build 2D plots.

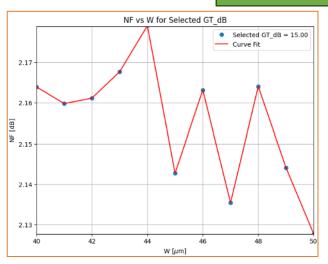
For a particular G_T

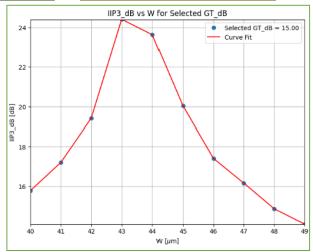
=> We get the relationship $q_S <=> W$

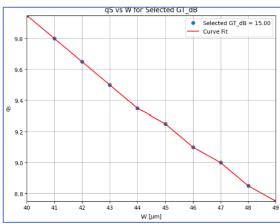
=> We plot NF(W)

=> We plot IIP3(W)

 q_S







W(µm)



Setting the final value:

- We choose W, that gives q_S for a given G_T .
- $(W;q_S)$ gives R_0 , R_L , I_D , G_m , V_{DSAT} and V_G

Input Matching

• With
$$R_0$$
, R_F , $G_m => R_P$

$$\Re(Zp) = R_P = rac{R_O + R_F}{1 + G_m R_O},$$

• With
$$R_S$$
 and R_P calculate \mathcal{Q}_P

With
$$R_S$$
 and R_P calculate Q_P $\Re(Z_{IN}) = R_S = \frac{R_P}{(1+Q_P^2)} = 50 \ \Omega$

$$ullet$$
 With Q_P calculate C_T and C_{GS}

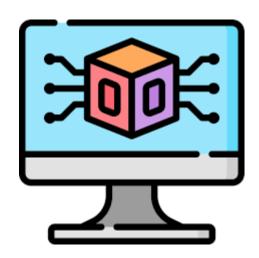
With
$$Q_P$$
 calculate C_T and C_{GS} ' $Q_P=R_PC_T\omega_0$ $C_T=C_{GS}+C_{GS}'+C_P$ $C_P=rac{R_O^2C_L(G_mR_F-1)}{(R_O+R_F)^2}$

$$ullet$$
 With C_T calculate L_G

$$\Im(Z_{IN}) = 0 = L_G s + \frac{Q_P^2}{C_T s (1 + Q_P)^2}$$



Now, let's simulate with a real PDK





T Acknowledgments











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